

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-12	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current V _{GS} = -4.5V (Note 6)	Steady State	T _A = +25°C T _A = +70°C	I _D	-11 -8.7	A
	t < 5s	T _A = +25°C T _A = +70°C	I _D	-15 -12	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-70	A
Maximum Body Diode Continuous Current (Note 6)			I _S	-2.5	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	-24	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	31	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	152	°C/W
	t < 5s		81	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	63	°C/W
	t < 5s		34	
Thermal Resistance, Junction to Case (Note 6)	Steady State	R _{θJC}	15	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-12	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -9.6V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.3	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	8.3	11	mΩ	V _{GS} = -4.5V, I _D = -5A
			9	14		V _{GS} = -3.7V, I _D = -5A
			12	19		V _{GS} = -2.5V, I _D = -4A
			16	30		V _{GS} = -1.8V, I _D = -1A
Diode Forward Voltage	V _{SD}	—	-0.8	-1.2	V	V _{GS} = 0V, I _S = -10A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	1860	—	pF	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	498	—		
Reverse Transfer Capacitance	C _{rss}	—	416	—		
Gate Resistance	R _g	—	11	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	26	—	nC	V _{DS} = -6V, I _D = -10A
Total Gate Charge (V _{GS} = -8V)	Q _g	—	44	—		
Gate-Source Charge	Q _{gs}	—	3.3	—		
Gate-Drain Charge	Q _{gd}	—	8.1	—		
Turn-On Delay Time	t _{D(ON)}	—	7.0	—	ns	V _{DS} = -6V, V _{GS} = -4.5V, R _G = 1Ω, I _D = -8A
Turn-On Rise Time	t _R	—	10.6	—		
Turn-Off Delay Time	t _{D(OFF)}	—	62.2	—		
Turn-Off Fall Time	t _F	—	61	—		
Reverse Recovery Time	t _{RR}	—	34.4	—	ns	I _F = -12A, di/dt = 500A/µs
Reverse Recovery Charge	Q _{RR}	—	28.1	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

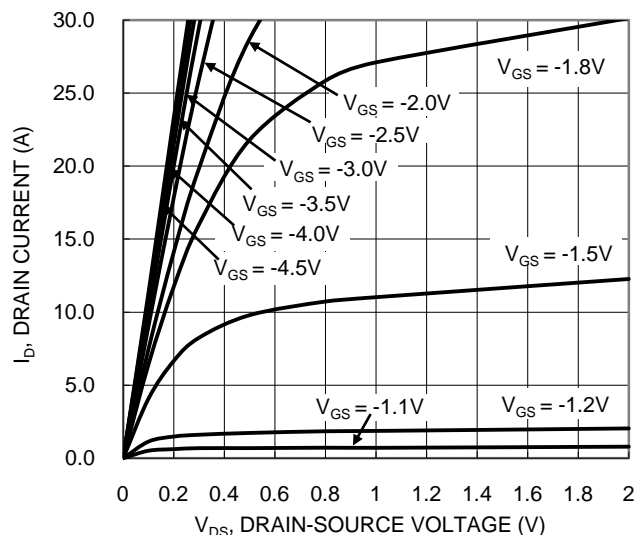


Figure 1. Typical Output Characteristic

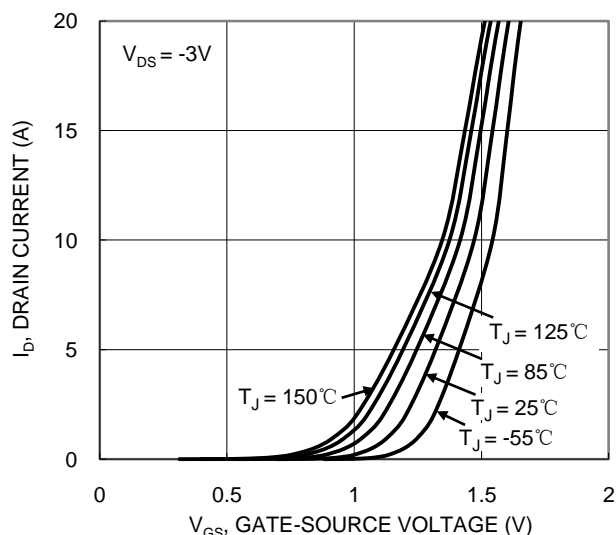


Figure 2. Typical Transfer Characteristic

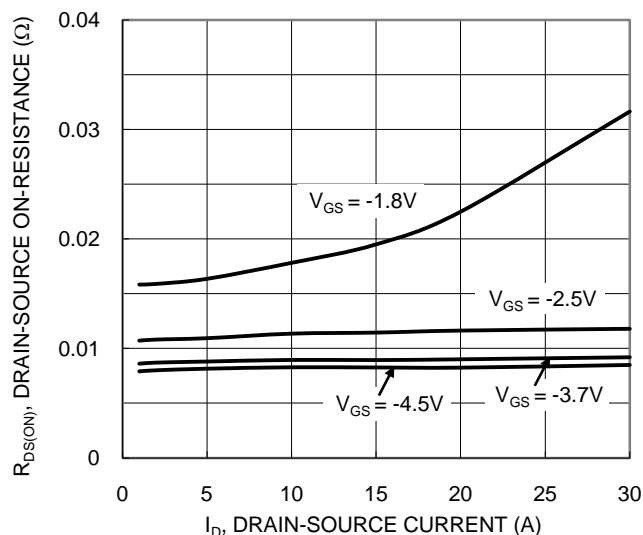


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

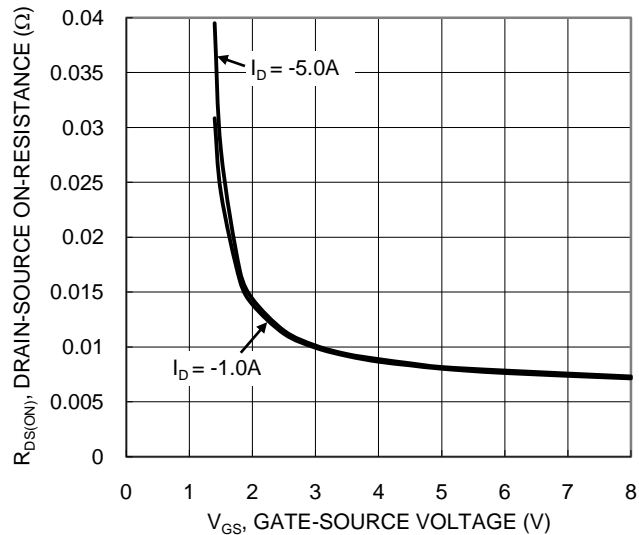


Figure 4. Typical Transfer Characteristic

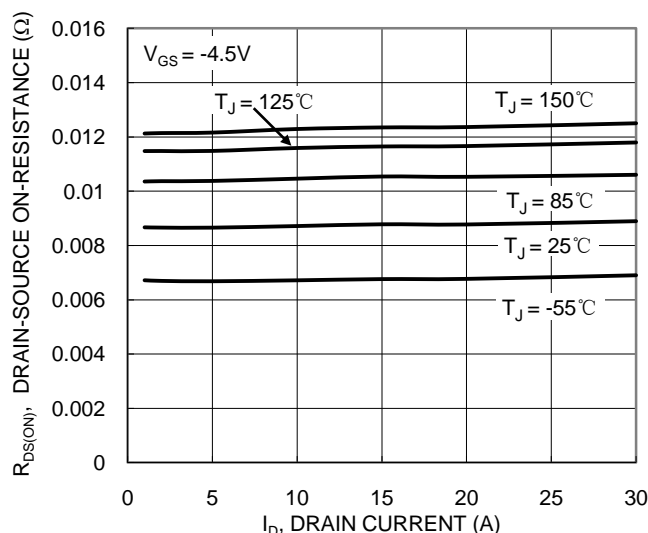


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

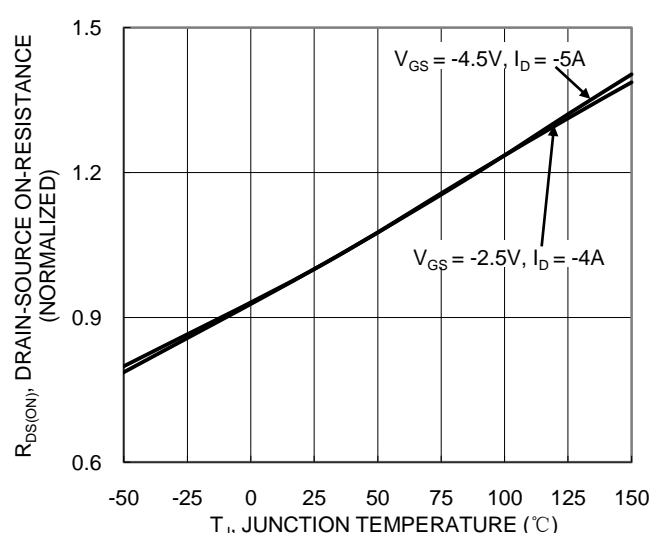
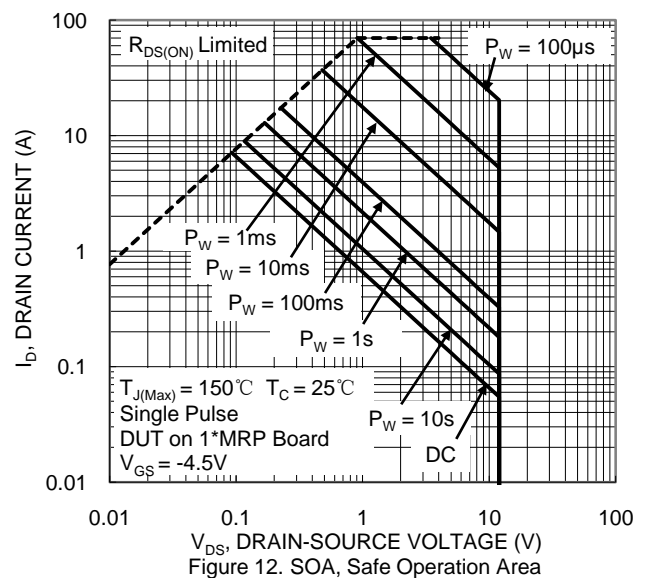
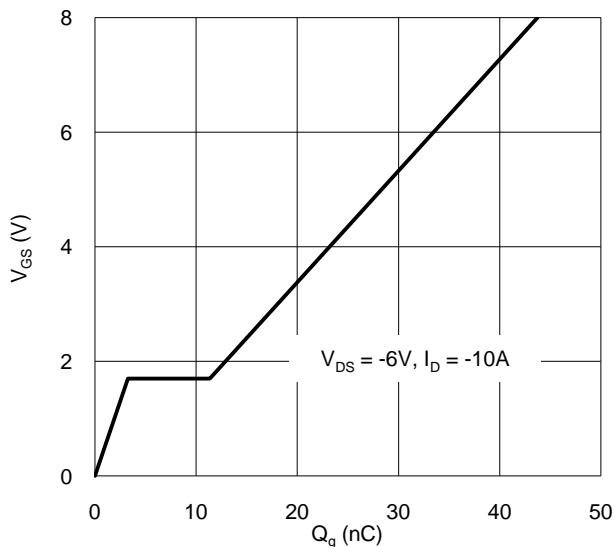
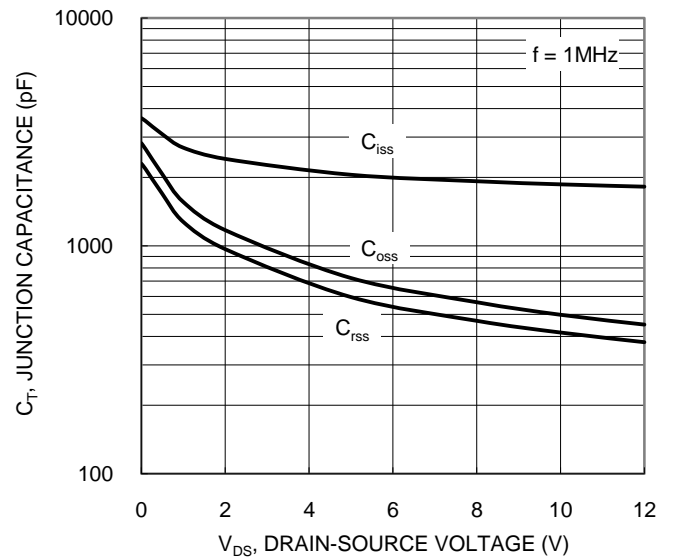
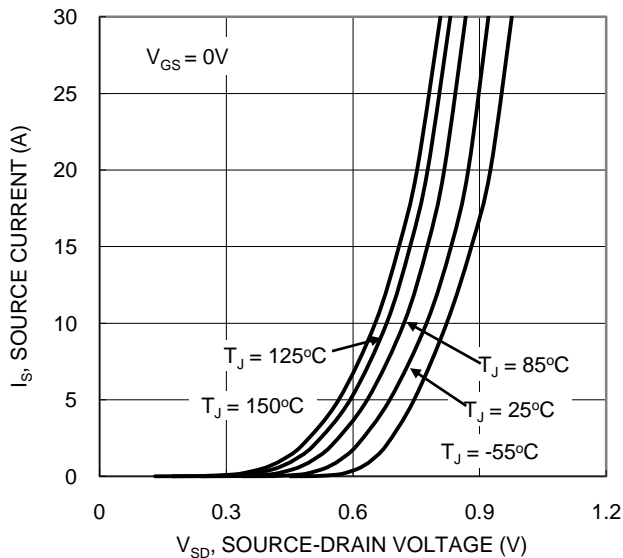
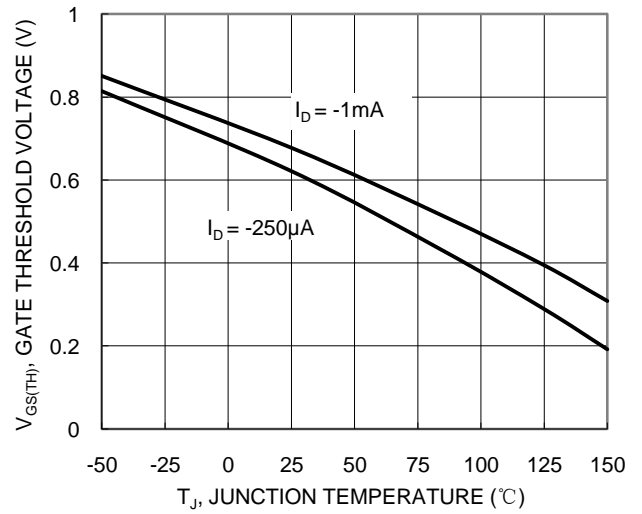
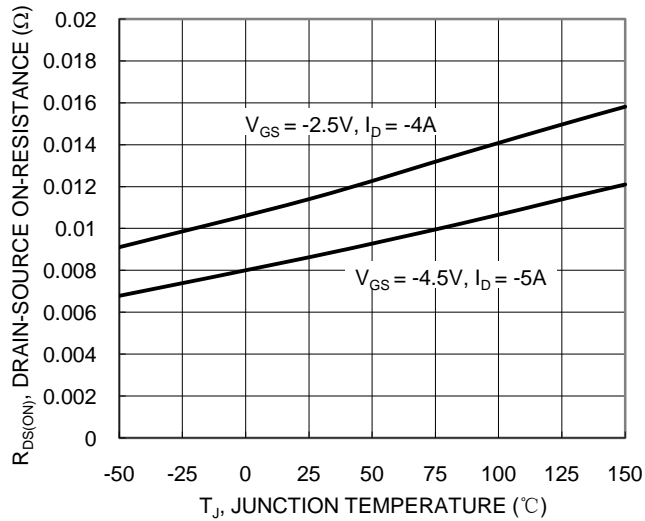


Figure 6. On-Resistance Variation with Temperature



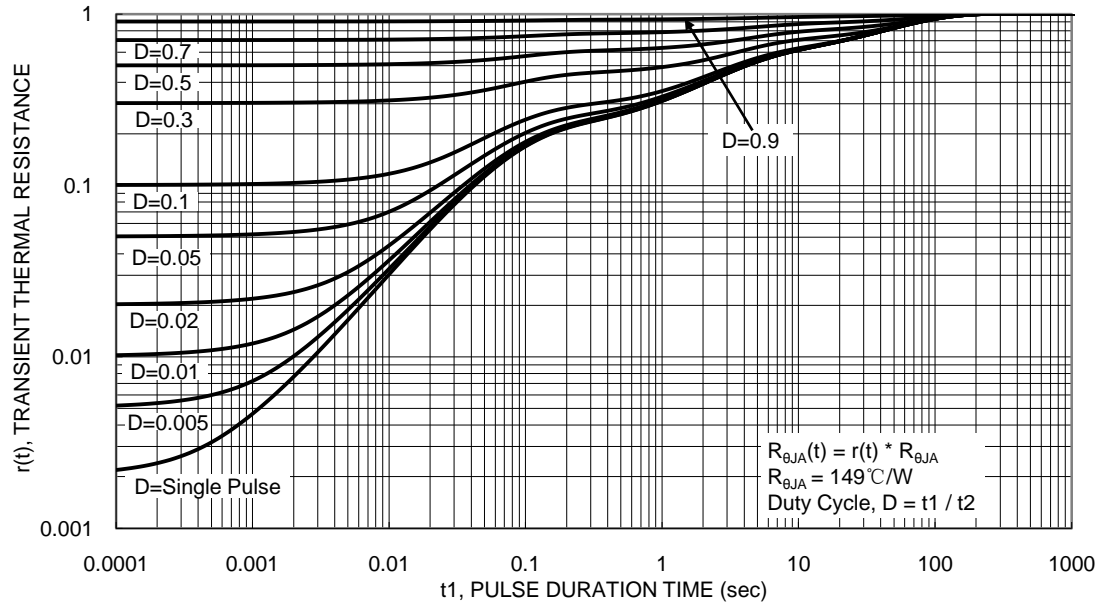
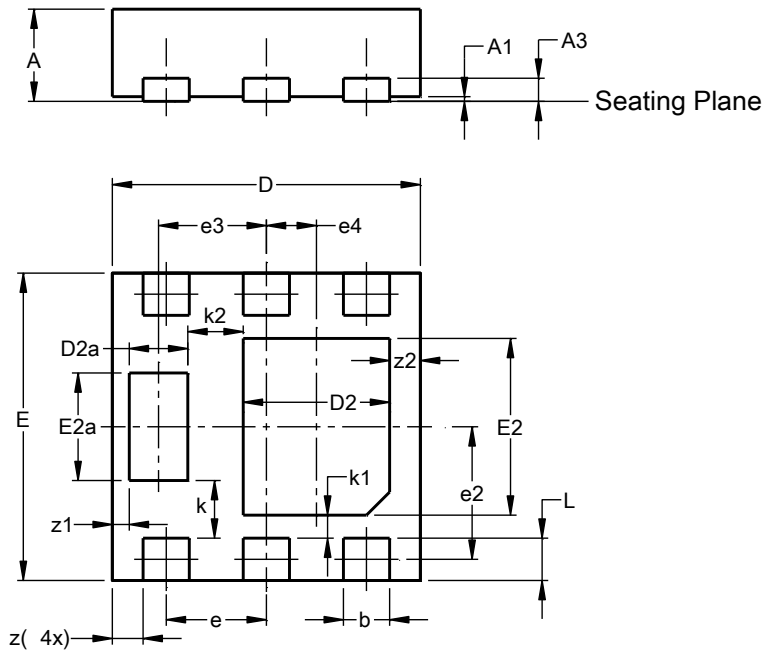


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)

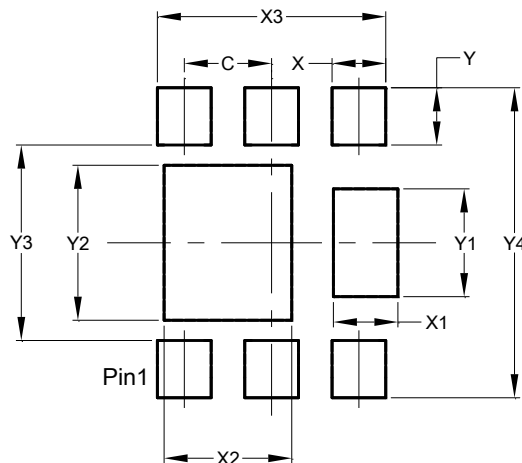


U-DFN2020-6 (Type F)			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65 BSC		
e2	0.863 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	0.37 BSC		
k1	0.15 BSC		
k2	0.36 BSC		
L	0.225	0.325	0.275
z	0.20 BSC		
z1	0.110 BSC		
z2	0.20 BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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